



芯长铭科技

MPCC10N120

Silicon Carbide Schottky Diode

Features

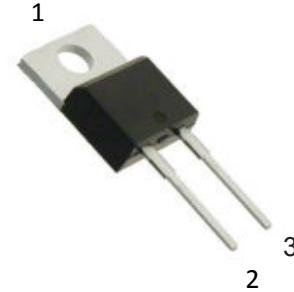
- Shorter recovery time
- Reduced temperature dependence
- High-speed switching possible
- High surge current capability

Construction

- Silicon carbide epitaxial planar type

Ordering Information

Type No.	Marking	Package Code
MPCC10N120	MPCC10N120	TO-220-2



TO-220-2



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1200	V		
V_{DC}	DC Blocking Voltage	1200	V		
I_F	Continuous Forward Current	34 19 10	A	$T_C=25^\circ\text{C}$ $T_C=125^\circ\text{C}$ $T_C=150^\circ\text{C}$	Fig. 7
I_{FRM}	Repetitive Peak Forward Surge Current	50	A	$T_C=25^\circ\text{C}$, $t_p=10\text{ ms}$, Half Sine Wave, $D=0.3$	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	70	A	$T_C=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave, $D=0.3$	
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	600	A	$T_C=25^\circ\text{C}$, $t_p=10\ \mu\text{s}$, Pulse	
P_{tot}	Power Dissipation	205 90	W	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	Fig. 6
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		



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Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.2	1.8	V	$I_F = 10\text{ A } T_J = 25^\circ\text{C}$ $I_F = 10\text{ A } T_J = 175^\circ\text{C}$	Fig. 1
I_R	Reverse Current	10 50	100 400	μA	$V_R = 1200\text{ V } T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V } T_J = 175^\circ\text{C}$	Fig. 2
Q_C	Total Capacitive Charge	50		nC	$V_R = 600\text{ V},$ $T_J = 25^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V)dV$	Fig. 4
C	Total Capacitance	610 46 40		pF	$V_R = 0\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 400\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 600\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$	Fig. 3
E_C	Capacitance Stored Energy	15		μJ	$V_R = 600\text{ V}$	Fig. 5

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.73	$^\circ\text{C/W}$	Fig. 8



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Typical Performance

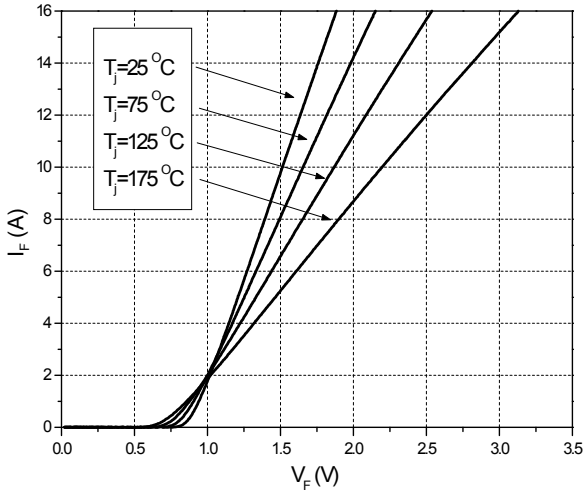


Figure 1. Forward Characteristics

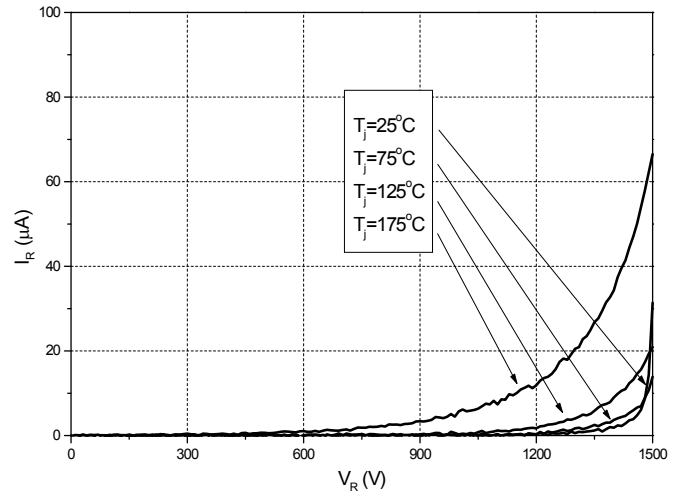


Figure 2. Reverse Characteristics

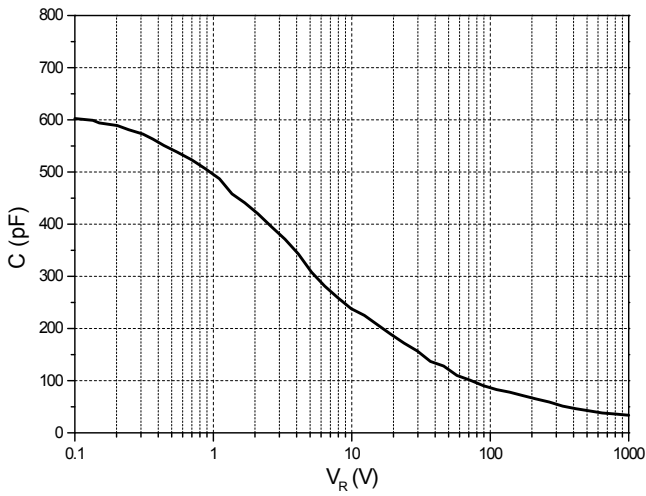


Figure 3. Capacitance vs. Reverse Voltage

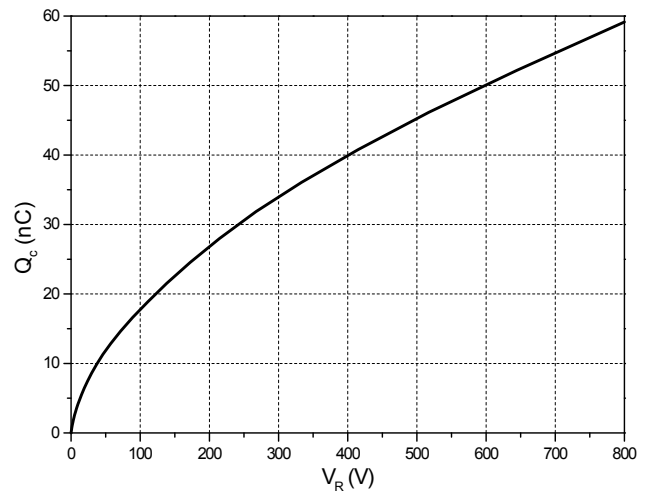


Figure 4. Total Capacitance Charge vs. Reverse Voltage



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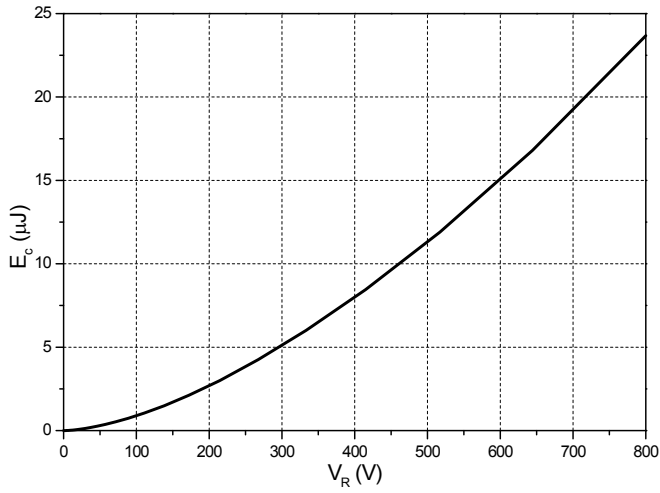


Figure 5. Capacitance Stored Energy

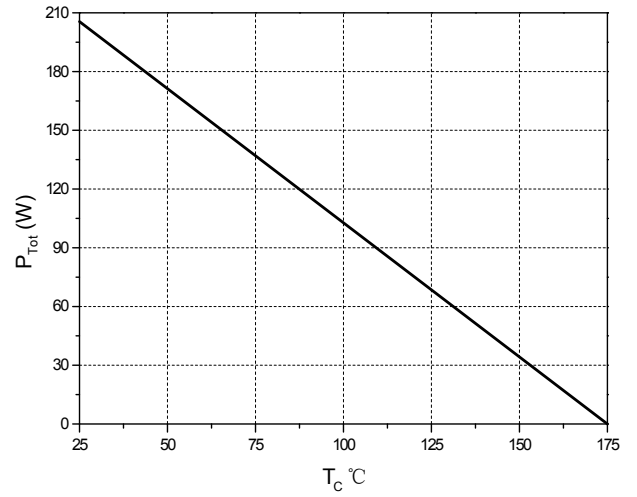


Figure 6. Power Derating

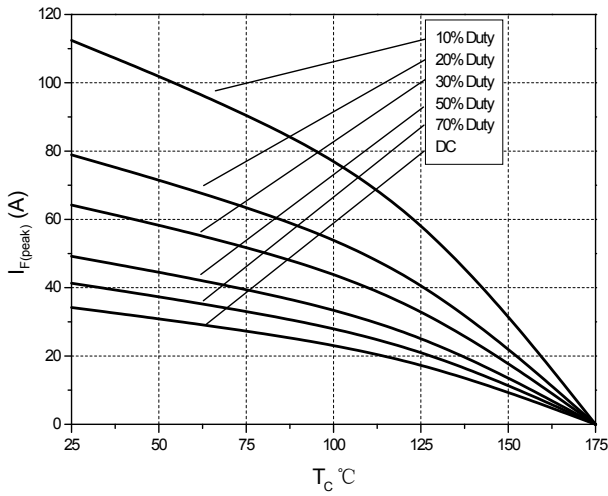


Figure 7. Current Derating

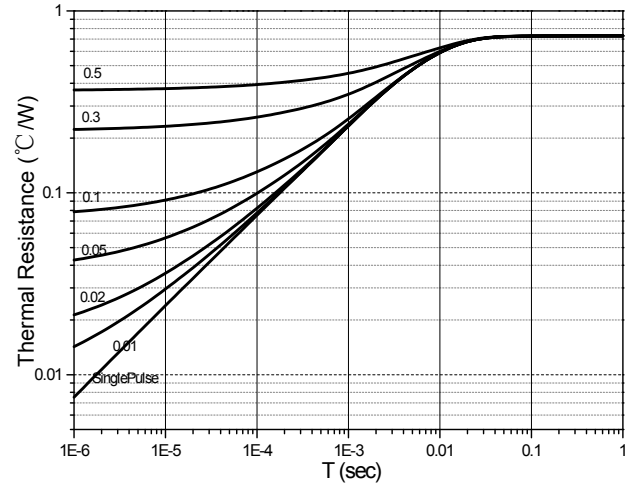


Figure 8. Transient Thermal Impedance